AMENDMENT TO THE SPECIFICATION

Before the first line of the specification, please replace the title with the following: paragraph at page 1, line 3, the following:
-- PULSED PLASMA CVD METHOD FOR FORMING A FILM --

Please accept the Abstract submitted on a separate sheet attached hereto as required by 37 C.F.R. 1.72(b).

In the specification, please replace the paragraph at page 4, line 25, beginning "In summary,..." with the following:
-- In summary, the process according to the present invention utilizes plasma glow ~~grow~~ discharge and comprises a known microwave plasma CVD process to which a magnetic field is added to utilize the interaction of the magnetic field with the high frequency (micro wave) electric field. However, the ECR conditions are omitted from the process. The process according to the present invention conducts the film deposition in a hybridized resonance space using a high density plasma having a high energy, under a high pressure in the range of from 0.03 to 30 Torr. In the process according to the present invention, the plasma excitation is carried out with a pulsed wave or a combination of a pulsed wave and a stationary continuous wave, as set forth above, under a high energy state in the hybridized resonance space to thereby generate active species at an increased amount and also to effect homogeneous nuclei formation on the surface of the substrate. This enables the formation of a thin film material at an excellent reproducibility. --

In the specification, please replace the paragraph at page 9, line 12, beginning "The magnetic field as shown in FIG. 1..." with the following:

-- The magnetic field as shown in FIG. 1 is generated by a Helmholtz coil system using two ring-shaped coils 5 and 5'. A quarter of the electric field and that of the magnetic field are shown in FIGs . 2(A) and 2(B) . Referring to FIG. 2(A), the abscissa

(X-axis) represents the horizontal direction (the direction in which the reactive gas is discharged) of the space 30, and the ordinate (R-axis) represents the direction along the diameter of the Helmholtz coil. The curves drawn in FIG. 2(A) represent the equipotential plane of the magnetic field. The numerals placed on the curves indicate the intensity of the magnetic field obtained when the magnetic intensity of the Helmholtz coil 5 is about 2000 Gauss. The magnetic field intensity over a large film-deposition area of the substrate in a region 100 in which the interaction between the electric field and the magnetic field occurs can be controlled to a nearly constant value (875 Gauss + 185 Gauss) by adjusting the strength of the magnet 5 , that is by adjusting current flowing through the Helmholtz coil 5. FIG. 2(A) shows the equipotential planes in a magnetic field; in particular, curve 26 is the equipotential plane in the magnetic field for 875 Gauss, which corresponds to the ECR condition. --